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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	84MHz
Connectivity	I ² C, IrDA, LINbus, SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	50
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	96K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f401rdt6tr

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3 Functional overview

3.1 ARM[®] Cortex[®]-M4 with FPU core with embedded Flash and SRAM

The ARM[®] Cortex[®]-M4 with FPU processor is the latest generation of ARM processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM[®] Cortex[®]-M4 with FPU 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices. The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution. Its single precision FPU (floating point unit) speeds up software development by using metalanguage development tools, while avoiding saturation.

The STM32F401xD/xE devices are compatible with all ARM tools and software.

Figure 3 shows the general block diagram of the STM32F401xD/xE.

Note: Cortex[®]-M4 with FPU is binary compatible with Cortex[®]-M3.

3.2 Adaptive real-time memory accelerator (ART Accelerator™)

The ART Accelerator™ is a memory accelerator which is optimized for STM32 industry-standard ARM[®] Cortex[®]-M4 with FPU processors. It balances the inherent performance advantage of the ARM[®] Cortex[®]-M4 with FPU over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher frequencies.

To release the processor full 105 DMIPS performance at this frequency, the accelerator implements an instruction prefetch queue and branch cache, which increases program execution speed from the 128-bit Flash memory. Based on CoreMark benchmark, the performance achieved thanks to the ART accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 84 MHz.

3.3 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

3.14 Power supply supervisor

3.14.1 Internal reset ON

This feature is available for V_{DD} operating voltage range 1.8 V to 3.6 V.

The internal power supply supervisor is enabled by holding PDR_ON high.

The device has an integrated power-on reset (POR) / power-down reset (PDR) circuitry coupled with a Brownout reset (BOR) circuitry. At power-on, POR is always active, and ensures proper operation starting from 1.8 V. After the 1.8 V POR threshold level is reached, the option byte loading process starts, either to confirm or modify default thresholds, or to disable BOR permanently. Three BOR thresholds are available through option bytes.

The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for an external reset circuit.

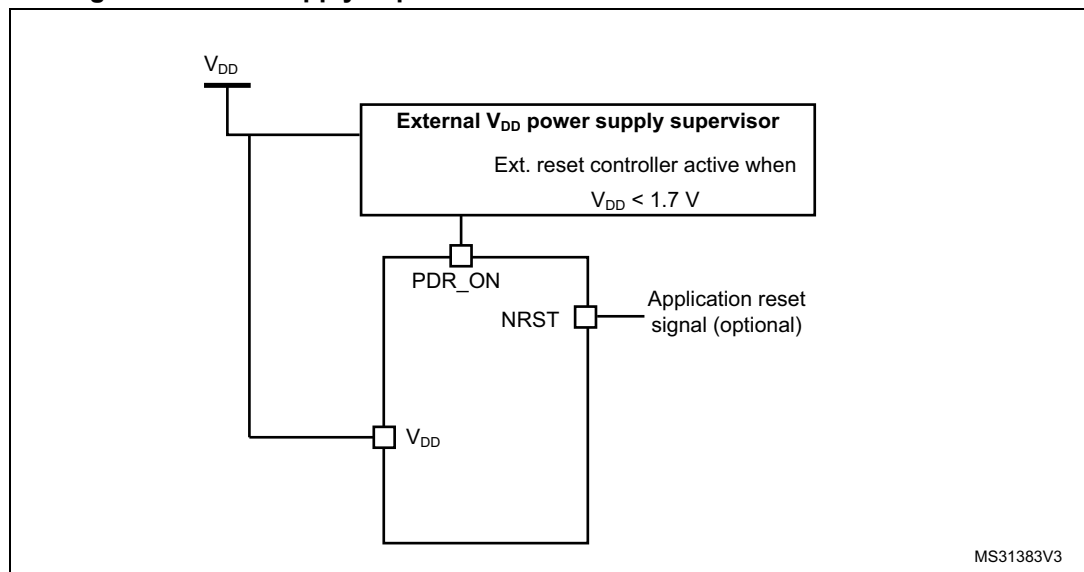
The device also features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.14.2 Internal reset OFF

This feature is available only on packages featuring the PDR_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled by setting the PDR_ON pin to low.

An external power supply supervisor should monitor V_{DD} and should maintain the device in reset mode as long as V_{DD} is below a specified threshold. PDR_ON should be connected to this external power supply supervisor. Refer to [Figure 5: Power supply supervisor interconnection with internal reset OFF](#).

Figure 5. Power supply supervisor interconnection with internal reset OFF⁽¹⁾



1. The PRD_ON pin is only available in the WLCSP49 and UFBGA100 packages.

The RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or from the V_{BAT} pin.

3.17 Low-power modes

The devices support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm/ wakeup/ tamper/ time stamp events).

- **Standby mode**

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm/ wakeup/ tamper/time stamp event occurs.

Standby mode is not supported when the embedded voltage regulator is bypassed and the 1.2 V domain is controlled by an external power.

3.18 V_{BAT} operation

The VBAT pin allows to power the device V_{BAT} domain from an external battery, an external super-capacitor, or from V_{DD} when no external battery and an external super-capacitor are present.

V_{BAT} operation is activated when V_{DD} is not present.

The VBAT pin supplies the RTC and the backup registers.

Note: When the microcontroller is supplied from VBAT, external interrupts and RTC alarm/events do not exit it from V_{BAT} operation. When PDR_ON pin is not connected to V_{DD} (internal Reset OFF), the V_{BAT} functionality is no more available and VBAT pin should be connected to V_{DD} .

If configured as standard 16-bit timers, it has the same features as the general-purpose TIMx timers. If configured as a 16-bit PWM generator, it has full modulation capability (0-100%).

The advanced-control timer can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

TIM1 supports independent DMA request generation.

3.19.2 General-purpose timers (TIMx)

There are seven synchronizable general-purpose timers embedded in the STM32F401xD/xE (see [Table 4](#) for differences).

- **TIM2, TIM3, TIM4, TIM5**

The STM32F401xD/xE devices are 4 full-featured general-purpose timers: TIM2, TIM5, TIM3, and TIM4. The TIM2 and TIM5 timers are based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. The TIM3 and TIM4 timers are based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They all feature four independent channels for input capture/output compare, PWM or one-pulse mode output. This gives up to 15 input capture/output compare/PWMs.

The TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together, or with the other general-purpose timers and the advanced-control timers TIM1 and TIM8 via the Timer Link feature for synchronization or event chaining.

Any of these general-purpose timers can be used to generate PWM outputs.

TIM2, TIM3, TIM4, TIM5 all have independent DMA request generation. They are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 4 hall-effect sensors.

- **TIM9, TIM10 and TIM11**

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM10 and TIM11 feature one independent channel, whereas TIM9 has two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4, TIM5 full-featured general-purpose timers. They can also be used as simple time bases.

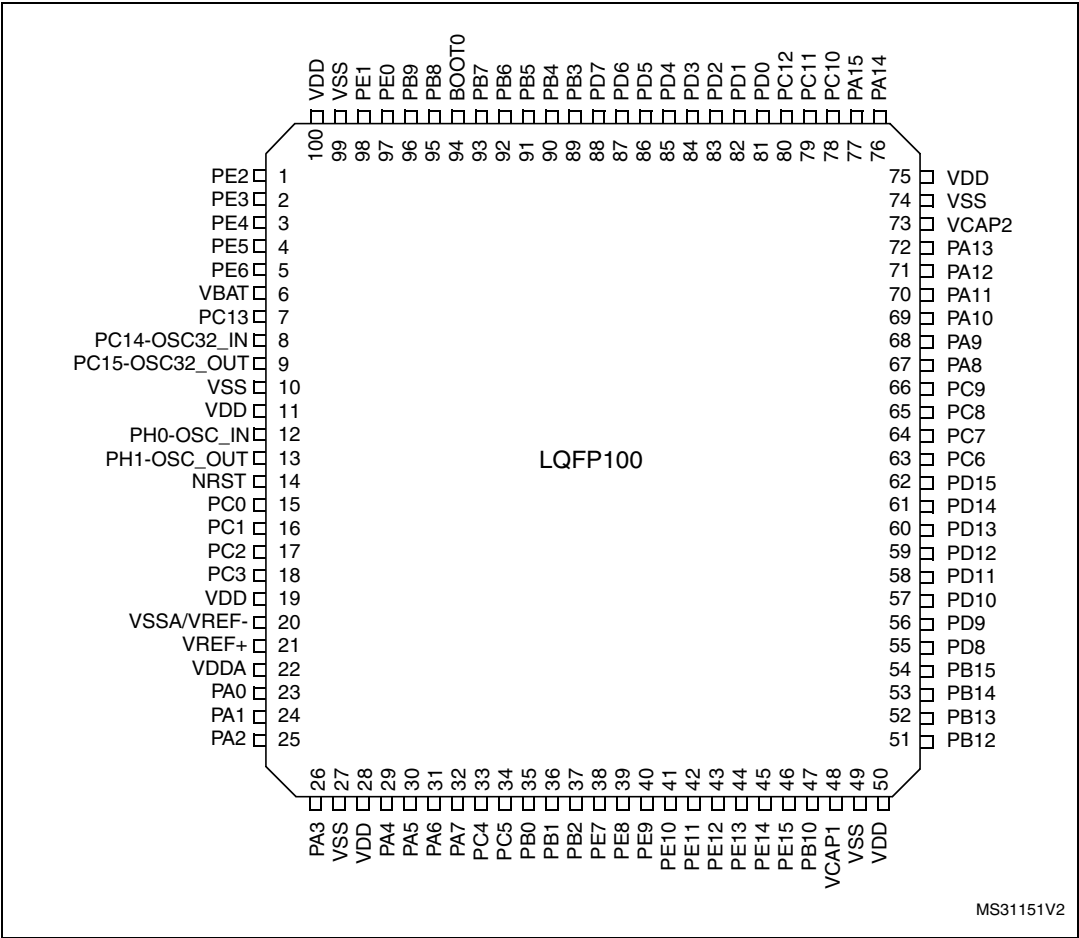
3.19.3 Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 32 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes.

3.19.4 Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

Figure 13. STM32F401xD/xE LQFP100 pinout

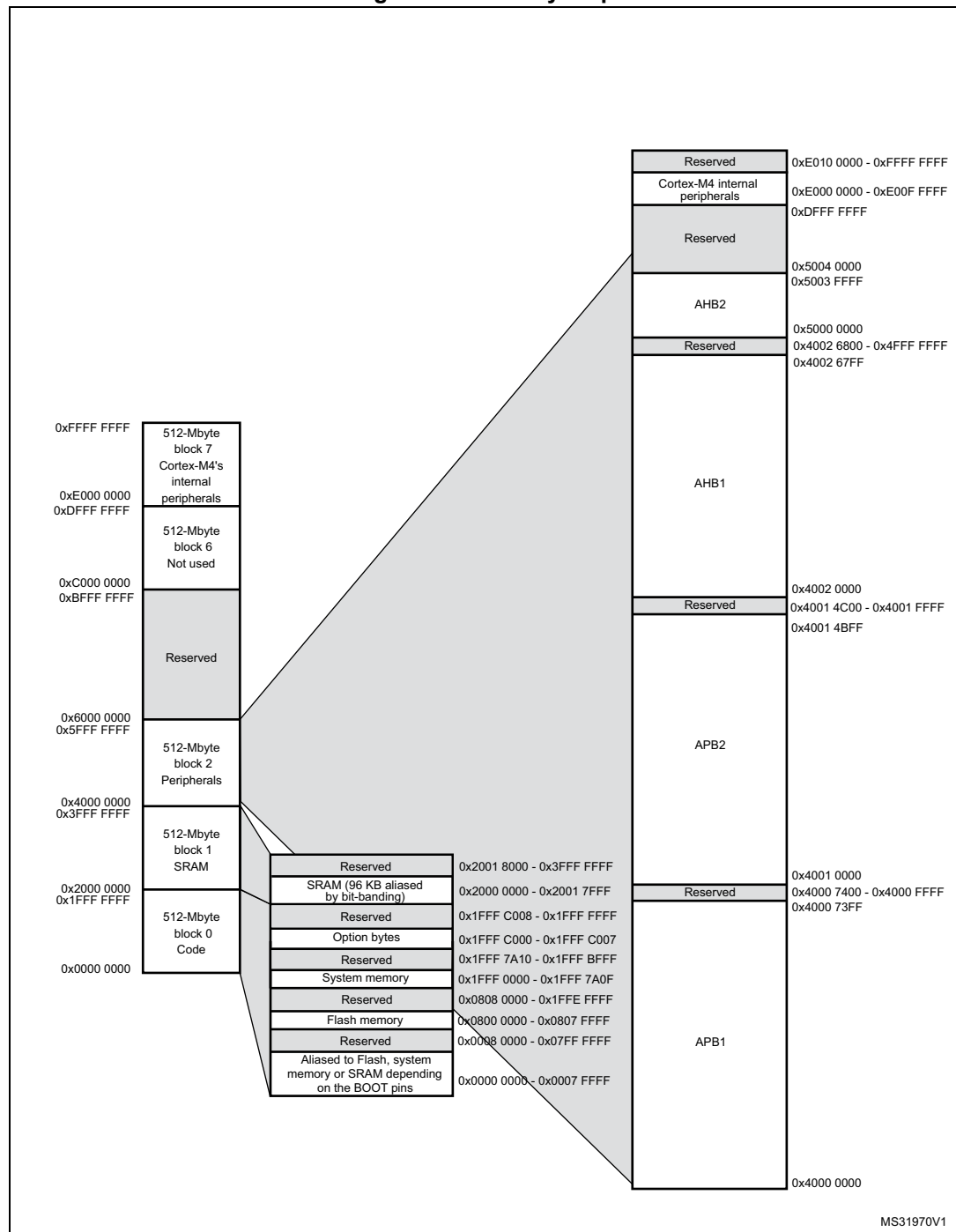


1. The above figure shows the package top view.

5 Memory mapping

The memory map is shown in *Figure 15*.

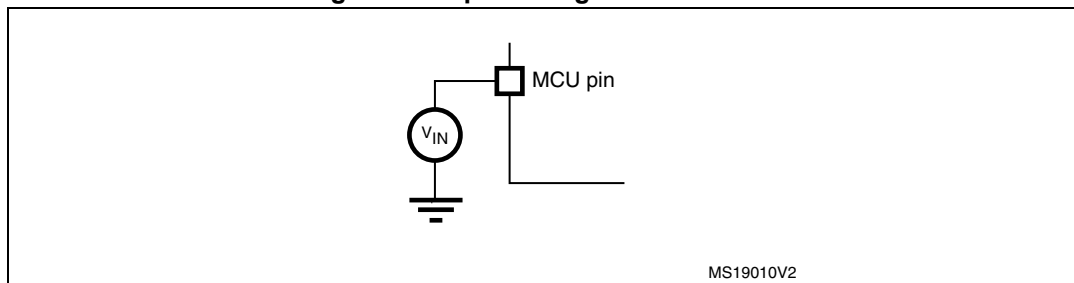
Figure 15. Memory map



6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 17](#).

Figure 17. Input voltage measurement



6.3 Operating conditions

6.3.1 General operating conditions

Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HCLK}	Internal AHB clock frequency	Power Scale3: Regulator ON, VOS[1:0] bits in PWR_CR register = 0x01	0	-	60	MHz
		Power Scale2: Regulator ON, VOS[1:0] bits in PWR_CR register = 0x10	0	-	84	
f_{PCLK1}	Internal APB1 clock frequency		0	-	42	
f_{PCLK2}	Internal APB2 clock frequency		0	-	84	
V_{DD}	Standard operating voltage		1.7 ⁽¹⁾	-	3.6	V
V_{DDA} (2)(3)	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as V_{DD} ⁽⁴⁾	1.7 ⁽¹⁾	-	2.4	
	Analog operating voltage (ADC limited to 2.4 M samples)		2.4	-	3.6	
V_{BAT}	Backup operating voltage		1.65	-	3.6	
V_{12}	Regulator ON: 1.2 V internal voltage on V_{CAP_1}/V_{CAP_2} pins	VOS[1:0] bits in PWR_CR register = 0x01 Max frequency 60 MHz	1.08 ⁽⁵⁾	1.14	1.20 ⁽⁵⁾	
		VOS[1:0] bits in PWR_CR register = 0x10 Max frequency 84 MHz	1.20 ⁽⁵⁾	1.26	1.32 ⁽⁵⁾	
V_{12}	Regulator OFF: 1.2 V external voltage must be supplied on V_{CAP_1}/V_{CAP_2} pins	Max. frequency 60 MHz.	1.1	1.14	1.2	
		Max. frequency 84 MHz.	1.2	1.26	1.32	
V_{IN}	Input voltage on RST and FT pins ⁽⁶⁾	$2\text{ V} \leq V_{DD} \leq 3.6\text{ V}$	-0.3	-	5.5	
		$V_{DD} \leq 2\text{ V}$	-0.3	-	5.2	
	Input voltage on BOOT0 pin		0	-	9	
P_D	Maximum allowed package power dissipation for suffix 7 ⁽⁷⁾	UFQFPN48	-	-	625	mW
		WLCSP49	-	-	392	
		LQFP64	-	-	313	
		LQFP100	-	-	465	
		UFBGA100	-	-	323	

Table 20. Typical and maximum current consumption, code with data processing (ART accelerator disabled) running from SRAM - $V_{DD} = 1.7\text{ V}$

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max ⁽¹⁾			Unit
				$T_A = 25\text{ °C}$	$T_A = 25\text{ °C}$	$T_A = 85\text{ °C}$	$T_A = 105\text{ °C}$	
I_{DD}	Supply current in Run mode	External clock, all peripherals enabled ⁽²⁾⁽³⁾	84	21.8	23.1	24.1	25.3 ⁽⁴⁾	mA
			60	15.8	16.5	17.5	18.7	
			40	11.4	11.9	12.9	13.9	
			20	6.0	6.3	7.3	8.3	
		External clock, all peripherals disabled ⁽³⁾	84	12.7	13.5	14.5	16.3 ⁽⁴⁾	
			60	9.2	10.5	11.5	12.8	
			40	6.7	7.1	8.1	9.1	
			20	3.6	3.8	4.8	5.8	

1. Guaranteed by characterization, not tested in production unless otherwise specified
2. When analog peripheral blocks such as ADC, HSE, LSE, HSI, or LSI are ON, an additional power consumption has to be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA for the analog part.
4. Tested in production.

Table 21. Typical and maximum current consumption, code with data processing (ART accelerator disabled) running from SRAM

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max ⁽¹⁾			Unit
					$T_A = 25\text{ °C}$	$T_A = 85\text{ °C}$	$T_A = 105\text{ °C}$	
I_{DD}	Supply current in Run mode	External clock, all peripherals enabled ⁽²⁾⁽³⁾	84	22.0	23.1	24.1	25.3	mA
			60	16.0	16.9	17.9	19.8	
			40	11.6	12.1	13.1	14.1	
			20	6.2	6.5	7.5	8.5	
		External clock, all peripherals disabled ⁽³⁾	84	12.9	14.0	15.0	16.3	
			60	9.5	10.5	11.5	12.8	
			40	6.9	7.3	8.3	9.3	
			20	3.8	4.0	5.0	6.0	

1. Guaranteed by characterization, not tested in production unless otherwise specified
2. When analog peripheral blocks such as ADC, HSE, LSE, HSI, or LSI are ON, an additional power consumption has to be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA for the analog part.

Table 26. Typical and maximum current consumption in Sleep mode

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ	Max ⁽¹⁾			Unit
					T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in Sleep mode	External clock, all peripherals enabled ⁽²⁾⁽³⁾	84	16.6	17.4	18.4	19.5	mA
			60	10.8	11.2	12.3	13.3	
			40	8.3	9.0	10.0	11.0	
			30	6.8	7.1	8.1	9.1	
			20	5.9	6.1	7.1	8.1	
		External clock, all peripherals disabled ⁽³⁾⁽⁴⁾	84	5.3	6.1	7.1	8.2	
			60	3.7	4.1	5.1	6.1	
			40	2.9	3.1	4.1	5.1	
			30	2.7	3.1	4.1	5.1	
			20	2.7	3.1	4.1	5.1	

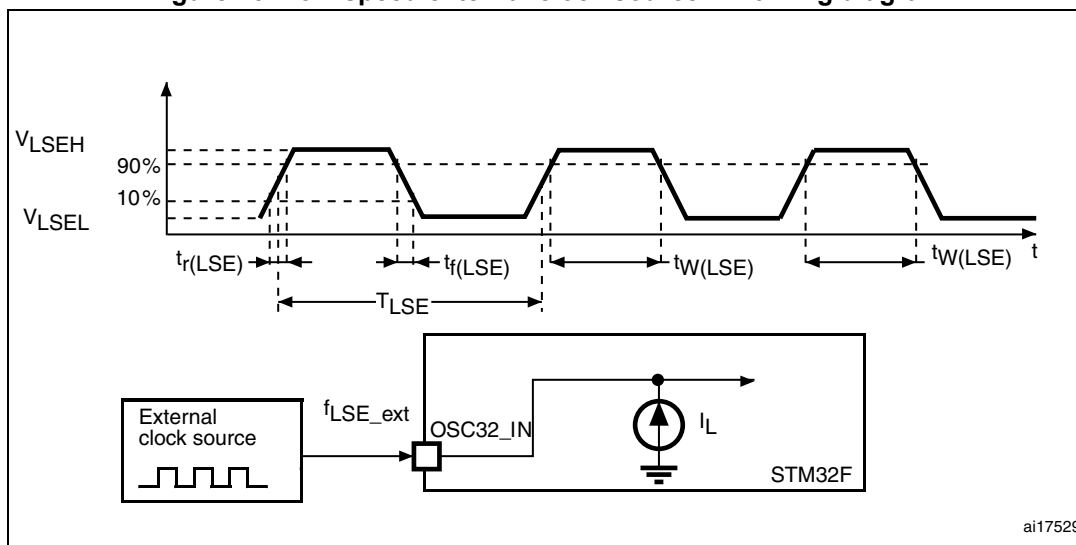
1. Guaranteed by characterization, not tested in production unless otherwise specified.
2. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA for the analog part.
4. Same current consumption for f_{HCLK} at 30 MHz and 20 MHz due to VCO running slower at 30 MHz.

Table 27. Typical and maximum current consumptions in Stop mode - V_{DD}=1.8 V

Symbol	Parameter	Conditions	Typ	Max ⁽¹⁾				Unit
			T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C		
I _{DD_STOP}	Main regulator usage	Flash in Stop mode, all oscillators OFF, no independent watchdog	109	135	440	650	μA	
	Low power regulator usage		41	65	310	530 ⁽²⁾		
	Main regulator usage	Flash in Deep power down mode, all oscillators OFF, no independent watchdog	72	95	345	530		
	Low power regulator usage		12	36	260	510 ⁽²⁾		
	Low power low voltage regulator usage		10	27	230	460		

1. Guaranteed by characterization, not tested in production.
2. Guaranteed by test in production.

Figure 23. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 37](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 37. HSE 4-26 MHz oscillator characteristics⁽¹⁾

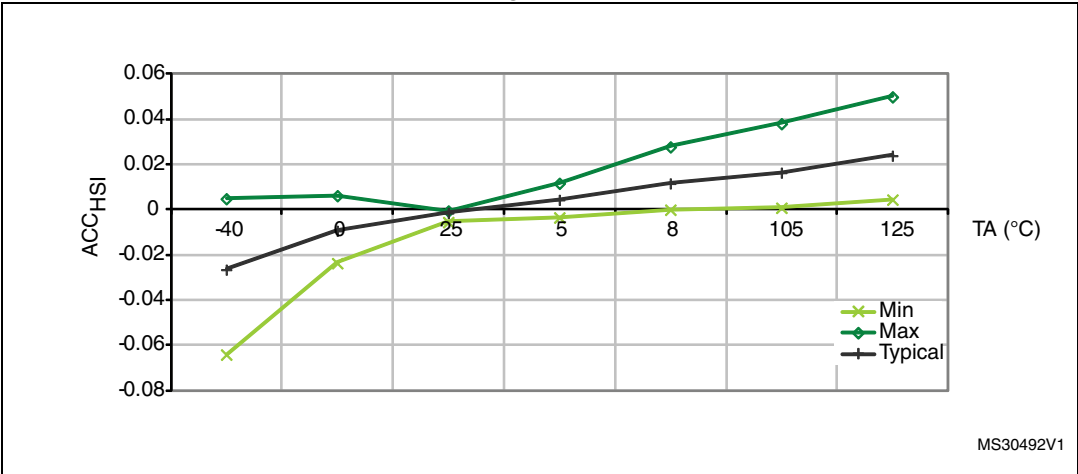
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency		4	-	26	MHz
R_F	Feedback resistor		-	200	-	k Ω
I_{DD}	HSE current consumption	$V_{DD}=3.3\text{ V}$, ESR= 30 Ω , $C_L=5\text{ pF @25 MHz}$	-	450	-	μA
		$V_{DD}=3.3\text{ V}$, ESR= 30 Ω , $C_L=10\text{ pF @25 MHz}$	-	530	-	
$G_{m_crit_max}$	Maximum critical crystal g_m	Startup	-	-	1	mA/V
$t_{SU(HSE)}^{(2)}$	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Guaranteed by design, not tested in production.

2. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see [Figure 24](#)). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the

Figure 26. ACC_{HSI} versus temperature



1. Guaranteed by characterization, not tested in production.

Low-speed internal (LSI) RC oscillator

Table 40. LSI oscillator characteristics ⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
$f_{LSI}^{(2)}$	Frequency	17	32	47	kHz
$t_{su(LSI)}^{(3)}$	LSI oscillator startup time	-	15	40	μs
$I_{DD(LSI)}^{(3)}$	LSI oscillator power consumption	-	0.4	0.6	μA

1. $V_{DD} = 3 V$, $T_A = -40$ to $105\text{ }^{\circ}C$ unless otherwise specified.

2. Guaranteed by characterization, not tested in production.

3. Guaranteed by design, not tested in production.

Table 41. Main PLL characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{DD(PLL)}^{(4)}$	PLL power consumption on VDD	VCO freq = 192 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLL)}^{(4)}$	PLL power consumption on VDDA	VCO freq = 192 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	

1. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between PLL and PLLI2S.
2. Guaranteed by design, not tested in production.
3. The use of 2 PLLs in parallel could degraded the Jitter up to +30%.
4. Guaranteed by characterization, not tested in production.

Table 42. PLLI2S (audio PLL) characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLLI2S_IN}	PLLI2S input clock ⁽¹⁾		0.95 ⁽²⁾	1	2.10	MHz
f_{PLLI2S_OUT}	PLLI2S multiplier output clock		-	-	216	
f_{VCO_OUT}	PLLI2S VCO output		192	-	432	
t_{LOCK}	PLLI2S lock time	VCO freq = 192 MHz	75	-	200	μs
		VCO freq = 432 MHz	100	-	300	
Jitter ⁽³⁾	Master I2S clock jitter	Cycle to cycle at 12.288 MHz on 48 KHz period, N=432, R=5	RMS	-	90	ps
			peak to peak	-	±280	
		Average frequency of 12.288 MHz N = 432, R = 5 on 1000 samples	-	90	-	
	WS I2S clock jitter	Cycle to cycle at 48 KHz on 1000 samples	-	400	-	
$I_{DD(PLLI2S)}^{(4)}$	PLLI2S power consumption on VDD	VCO freq = 192 MHz	0.15	-	0.40	mA
		VCO freq = 432 MHz	0.45		0.75	
$I_{DDA(PLLI2S)}^{(4)}$	PLLI2S power consumption on VDDA	VCO freq = 192 MHz	0.30	-	0.40	
		VCO freq = 432 MHz	0.55		0.85	

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design, not tested in production.
3. Value given with main PLL running.
4. Guaranteed by characterization, not tested in production.

Table 45. Flash memory programming

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
t_{prog}	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100 ⁽²⁾	μs
$t_{\text{ERASE16KB}}$	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	400	800	ms
		Program/erase parallelism (PSIZE) = x 16	-	300	600	
		Program/erase parallelism (PSIZE) = x 32	-	250	500	
$t_{\text{ERASE64KB}}$	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1200	2400	ms
		Program/erase parallelism (PSIZE) = x 16	-	700	1400	
		Program/erase parallelism (PSIZE) = x 32	-	550	1100	
$t_{\text{ERASE128KB}}$	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	2	4	s
		Program/erase parallelism (PSIZE) = x 16	-	1.3	2.6	
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
t_{ME}	Mass erase time	Program/erase parallelism (PSIZE) = x 8	-	8	16	s
		Program/erase parallelism (PSIZE) = x 16	-	5.5	11	
		Program/erase parallelism (PSIZE) = x 32	-	4	8	
V_{prog}	Programming voltage	32-bit program operation	2.7	-	3.6	V
		16-bit program operation	2.1	-	3.6	V
		8-bit program operation	1.7	-	3.6	V

1. Guaranteed by characterization, not tested in production.

2. The maximum programming time is measured after 100K erase operations.

Table 46. Flash memory programming with V_{PP} voltage

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
t_{prog}	Double word programming	$T_{\text{A}} = 0 \text{ to } +40 \text{ }^{\circ}\text{C}$ $V_{\text{DD}} = 3.3 \text{ V}$ $V_{\text{PP}} = 8.5 \text{ V}$	-	16	100 ⁽²⁾	μs
$t_{\text{ERASE16KB}}$	Sector (16 KB) erase time		-	230	-	ms
$t_{\text{ERASE64KB}}$	Sector (64 KB) erase time		-	490	-	
$t_{\text{ERASE128KB}}$	Sector (128 KB) erase time		-	875	-	
t_{ME}	Mass erase time		-	1.750	-	s

Table 48. EMS characteristics for LQFP100 package

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP100, WLCSP49, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 84\text{ MHz}$, conforms to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP100, WLCSP49, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 84\text{ MHz}$, conforms to IEC 61000-4-4	4A

When the application is exposed to a noisy environment, it is recommended to avoid pin exposition to disturbances. The pins showing a middle range robustness are: PA0, PA1, PA2, on LQFP100 packages and PDR_ON on WLCSP49.

As a consequence, it is recommended to add a serial resistor (1 k Ω maximum) located as close as possible to the MCU to the pins exposed to noise (connected to tracks longer than 50 mm on PCB).

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

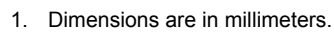
7 Package characteristics

7.1 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

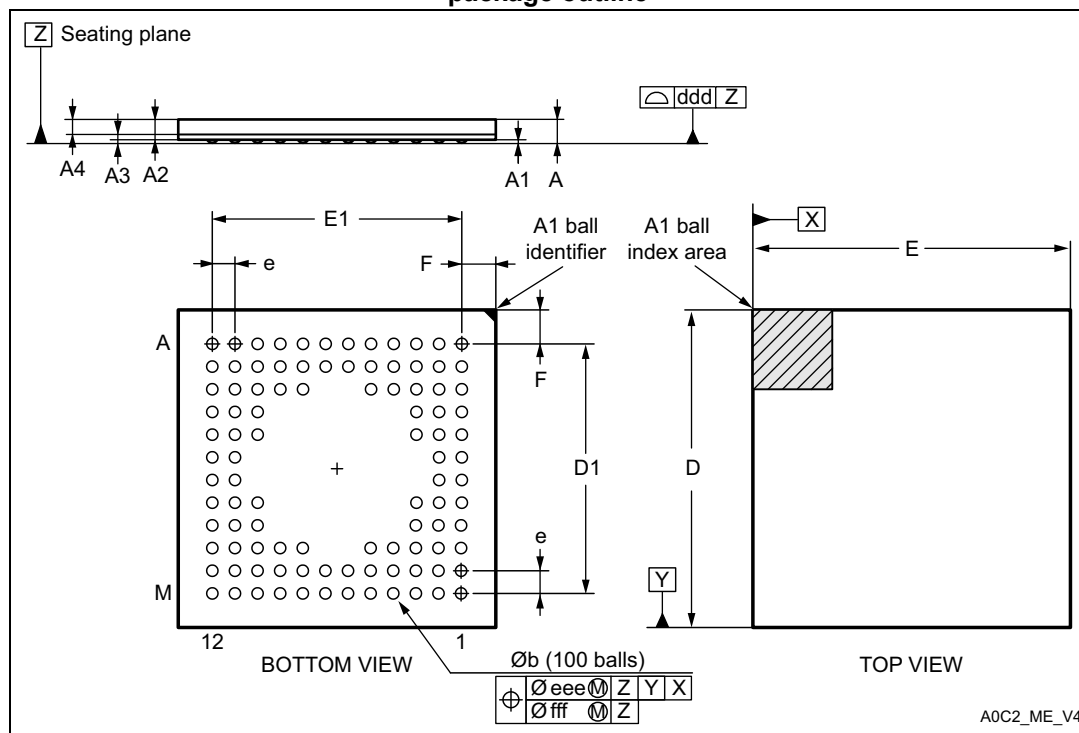
Symbol	millimeters			inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
T	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
e	-	0.500	-	-	0.0197	-

Figure 50. UFQFPN48 recommended footprint



7.1.5 UFBGA100, 7 x 7 mm, 0.5 mm pitch package

Figure 58. UFBGA100, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 84. UFBGA100, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.0020	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
A3	-	0.130	-	-	0.0051	-
A4	0.270	0.320	0.370	0.0106	0.0126	0.0146
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
D	6.950	7.000	7.050	0.2736	0.2756	0.2776
D1	5.450	5.500	5.550	0.2146	0.2165	0.2185
E	6.950	7.000	7.050	0.2736	0.2756	0.2776
E1	5.450	5.500	5.550	0.2146	0.2165	0.2185
e	-	0.500	-	-	0.0197	-
F	0.700	0.750	0.800	0.0276	0.0295	0.0315

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